

Abstract of the Disclosure

A method for fabricating an isolation layer in a semiconductor device is disclosed. The disclosed method comprises steps of: forming a trench on a semiconductor substrate; forming a flowing insulating layer within the trench; making the insulating layer precise; and forming a precise insulating layer over an upper surface of the whole structure on which the flowing insulating layer is formed. According to the method of fabricating an isolation layer in a semiconductor device, occurrence of fine pores at adjacent active regions of sidewalls in a trench can be prevented.